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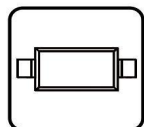
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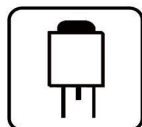
電源管理



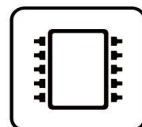
顯示驅動



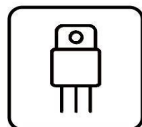
二三極管



LDO穩壓器



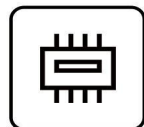
觸摸芯片



MOS管



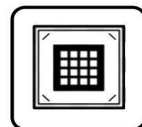
運算放大器



存儲芯片



MCU



串口通信

SS8550 Y2-TD(0.52)

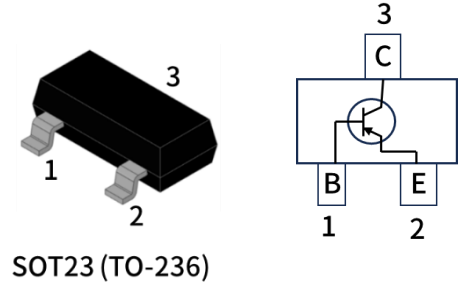
產品規格說明書

SS8550LST1

General Purpose Transistors PNP

1. FEATURES

- The material of product compliance with RoHS requirements and Halogen Free.
- High Stability and High Reliability.
- Complementary to SS8050LST1(NPN)
- High current capacity in compact package. IC =1.5 A.



2. Mechanical Data

- SOT-23 Small Outline Plastic Package.
- Tin plated leads, solderable per J-STD-002 and JESD22-B102.
- Marking: Y2

3. ORDERING INFORMATION

Device	Min Pack	Inner Box	Outer Carton	Reel
SS8550LST1	3000	45000	180000	7 inch

4. MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Limit	Unit
Collector-Emitter Voltage	VCEO	-25	V
Collector-Base Voltage	VCBO	-40	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current--Continuous	Ic	-1500	mA
Collector Power Dissipation	Pc	300	mW

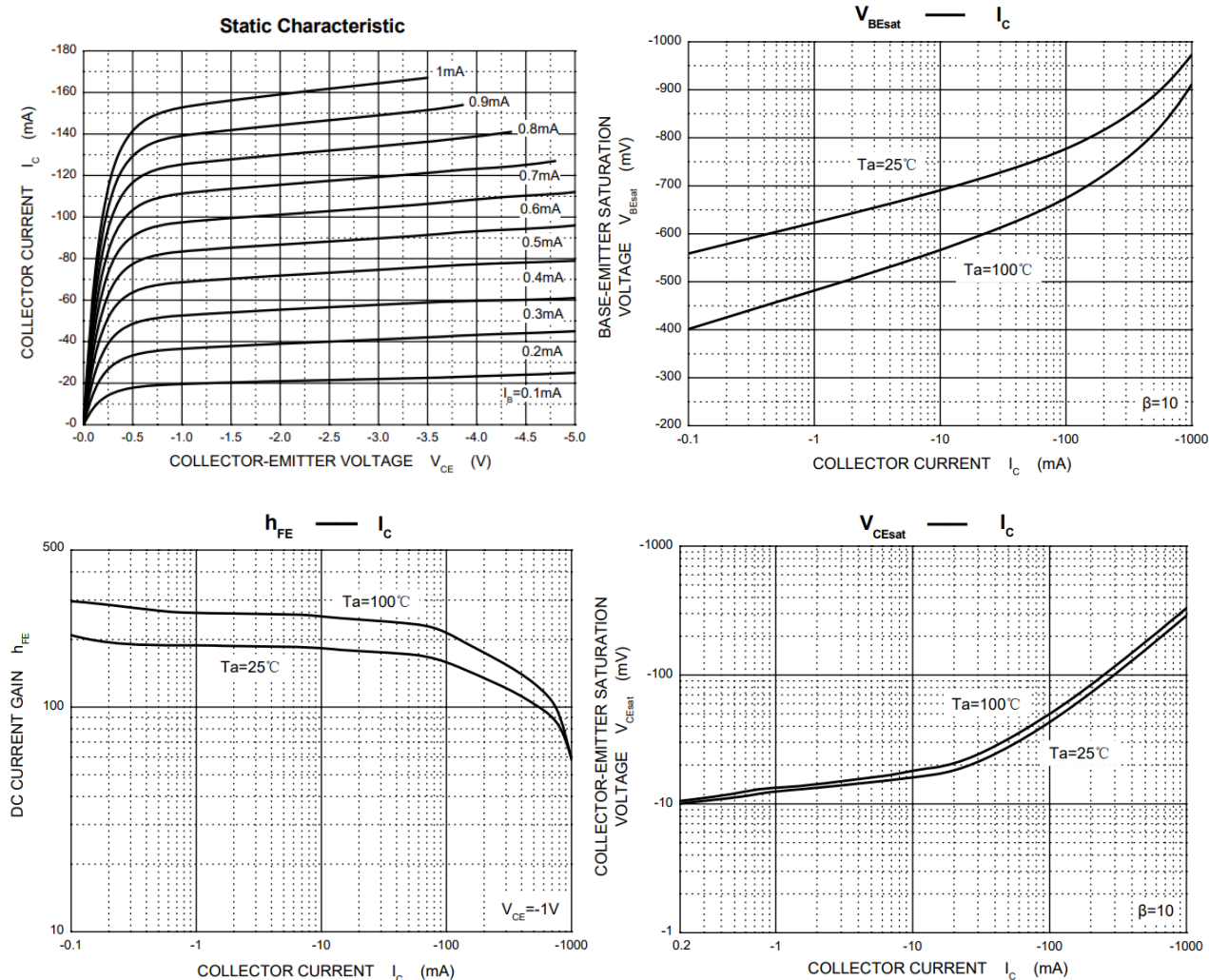
5. THERMAL CHARACTERISTICS

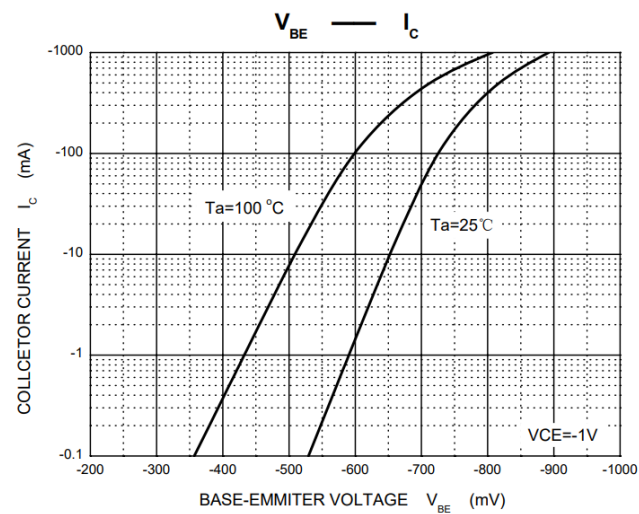
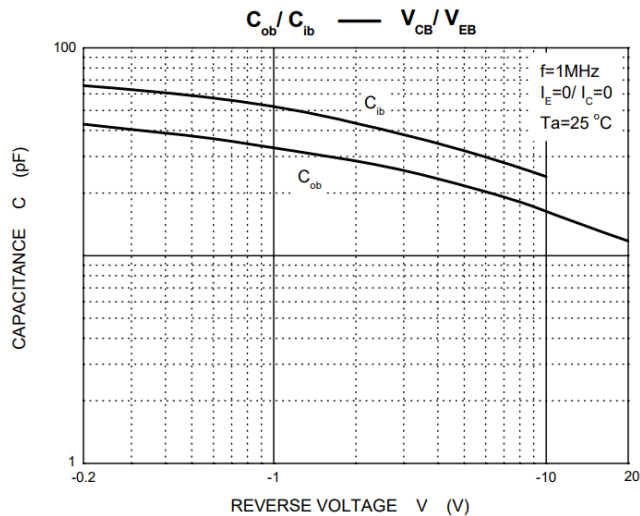
Parameter	Symbol	Limit	Unit
Operation Junction and Storage Temperature Range	TSTG	-55~150	°C
Thermal Resistance Junction to Ambient	RθJA	417	°C/W

6. ELECTRICAL CHARACTERISTICS (Ta= 25°C unless otherwise specified)

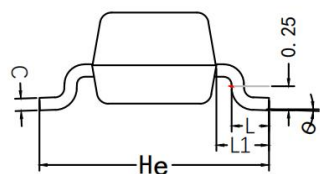
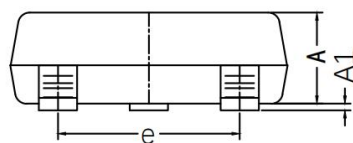
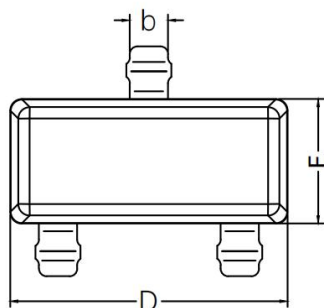
Parameter	Symbol	Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -0.1\text{mA}, I_B = 0$	-25		V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\text{ }\mu\text{A}, I_E = 0$	-40		V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\text{ }\mu\text{A}, I_C = 0$	-5		V
Collector Cutoff current	I_{CEO}	$V_{CE} = -20\text{ V}, I_B = 0$		-100	nA
Collector Cutoff Current	I_{CBO}	$V_{CB} = -40\text{ V}, I_E = 0$		-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$		-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{ V}, I_C = -5\text{ mA}$	60		
DC current gain	$h_{FE(2)}$	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$	120	350	
DC current gain	$h_{FE(3)}$	$V_{CE} = -1\text{ V}, I_C = -800\text{ mA}$	50		
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{ mA}, I_B = -80\text{ mA}$		-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -800\text{ mA}, I_B = -80\text{ mA}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -50\text{ mA}, f = 30\text{ MHz}$	100		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		20	pF

7. ELECTRICAL CHARACTERISTICS CURVES





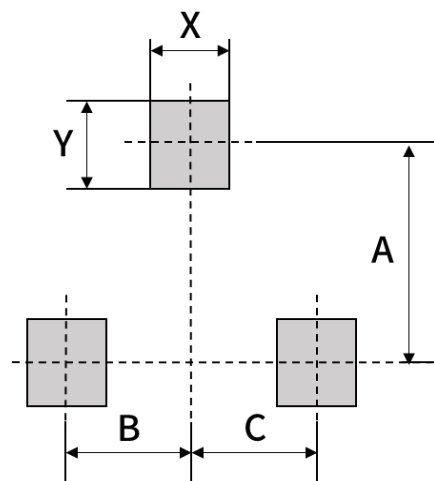
8. OUTLINE AND DIMENSIONS



DIM	MIN	NOR	MAX
A	0.85	0.95	1.05
A1	0.01	0.06	0.10
b	0.36	0.44	0.52
c	0.09	0.13	0.18
D	2.80	2.90	3.10
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.40	0.50
L1	0.35	0.50	0.65
He	2.10	2.35	2.50
θ	0°	—	10°

All Dimensions in mm

9. SUGGESTED PAD LAYOUT



SOT23		
DIM	mm	inch
A	2.00	0.079
B	0.95	0.037
C	0.95	0.037
X	0.80	0.031
Y	0.90	0.035